

-30V P-Channel Enhancement Mode Power MOSFET

MAIN CHARACTERISTICS

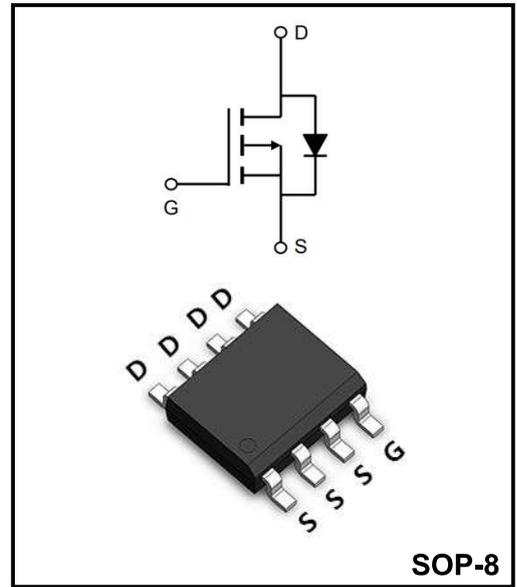
I_D	-5.3A
V_{DSS}	-30V
R_{DS(on)-typ(@V_{GS}=-10V)}	<55mΩ(Typ:45mΩ)
R_{DS(on)-typ(@V_{GS}=-4.5V)}	<85mΩ(Typ:65mΩ)

FEATURES

- ◆ High Power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

Applications

- ◆ PWM applications
- ◆ Load switch
- ◆ Power management



Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Characteristics	Symbols	Value	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate - Source Voltage	V_{GS}	±20	V
Drain Current – Continuous	I_D	-5.3	A
Pulsed Drain Current ^(Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	2.5	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C
Thermal Resistance, Junction-to-Ambient ^(Note 2)	R_{θJA}	49	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	BV_{DSS}	-30	-33	-	V
Drain -Source Leakage Current	V _{DS} =-24V, V _{GS} =0V	I_{DSS}	-	-	-1	μA
Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	I_{GSS}	-	-	±100	nA
Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D =4.0A	R_{DS(ON)}	-	45	55	mΩ
	V _{GS} =- 4.5 V, I _D =3.0A		-	65	85	mΩ
Forward Transconductance	V _{DS} =-15V, I _D =-4.5A	g_{fs}	4	7	-	S
Input Capacitance	V _{DS} =-15V V _{GS} =0V F=1.0MHz	C_{iss}	-	1040	-	pF
Output Capacitance		C_{oss}	-	420	-	
Reverse Transfer Capacitance		C_{rss}	-	150	-	
Turn-on Delay Time	V _{DD} =-15V I _D =-1A V _{GS} =-10V R _{GEN} =6Ω	t_{d(on)}	-	15	-	ns
Turn-on Rise Time		T_r	-	13	-	
Turn-Off Delay Time		t_{d(OFF)}	-	58	-	
Turn-Off Fall Time		t_f	-	21	-	
Total Gate Charge	V _{DS} =-15V, I _D =-5.3A V _{GS} =-10V	Q_G		12	-	nC
Gate to Source Charge		Q_{GS}		2.2	-	
Gate to Drain Charge		Q_{GD}		3	-	
Diode Forward Voltage ^(Note 3)	V _{GS} =0V, I _S =-1.7A	V_{SD}	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

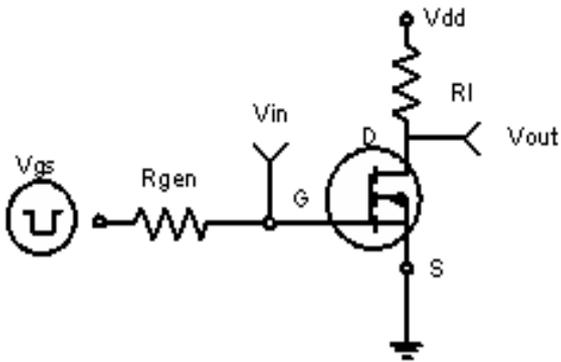


Figure 1: Switching Test Circuit

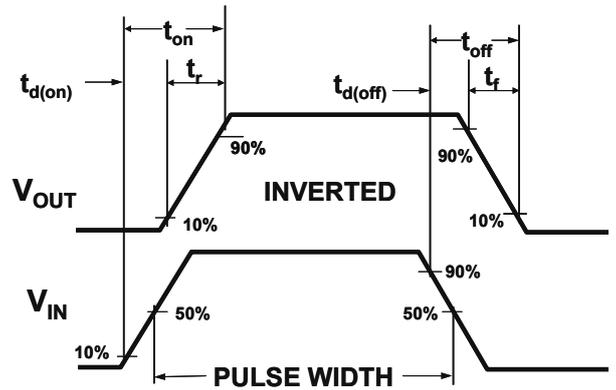


Figure 2: Switching Waveforms

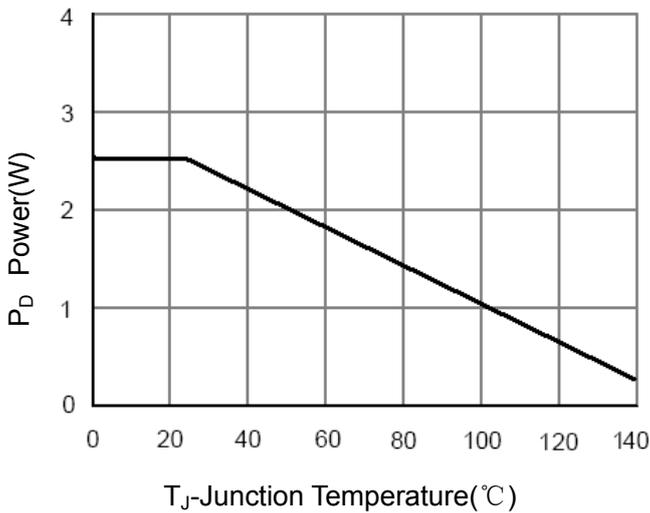


Figure 3 Power Dissipation

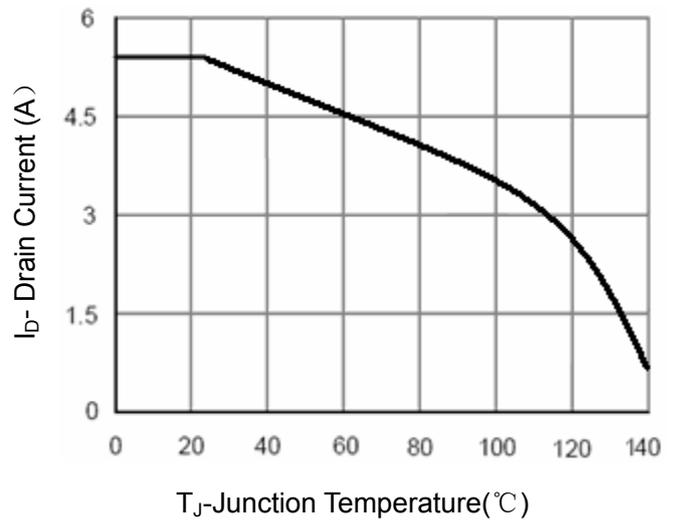


Figure 4 Drain Current

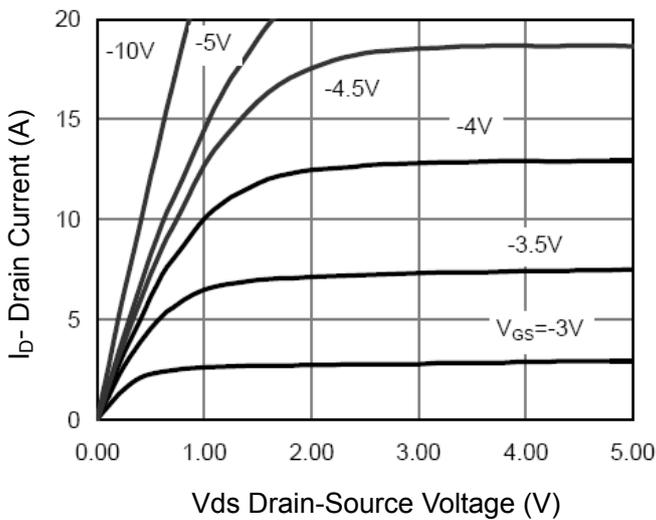


Figure 5 Output Characteristics

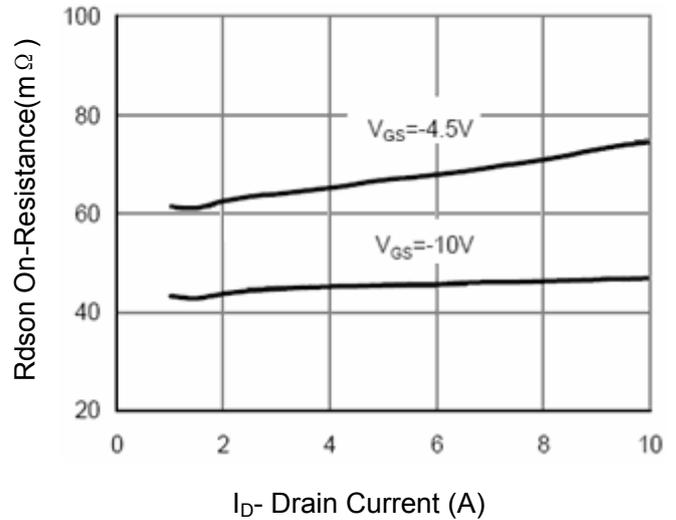
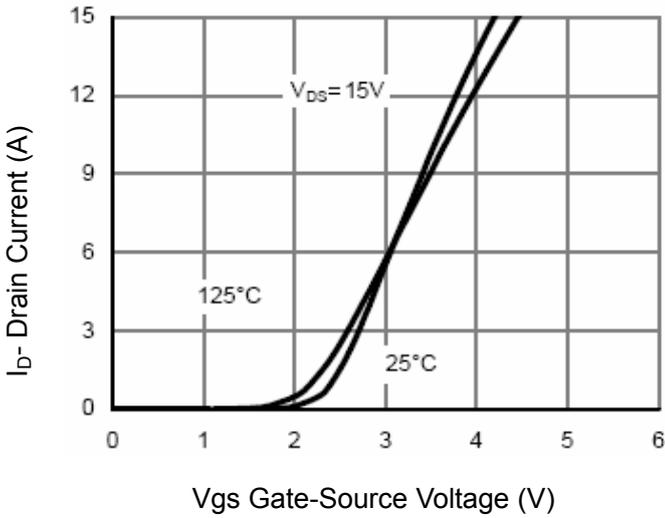
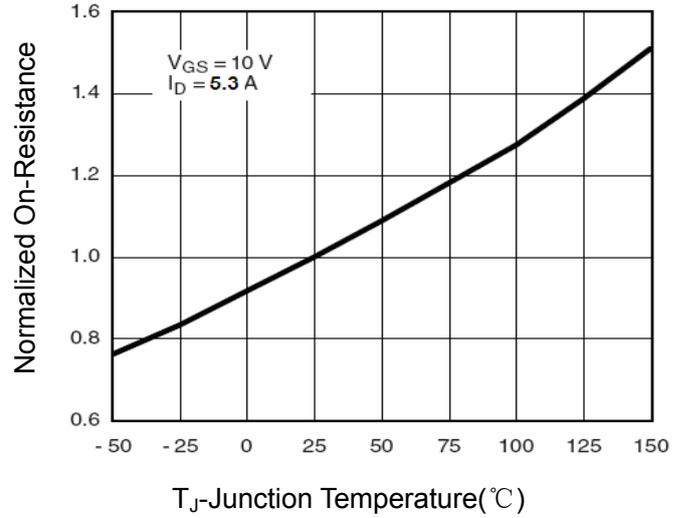


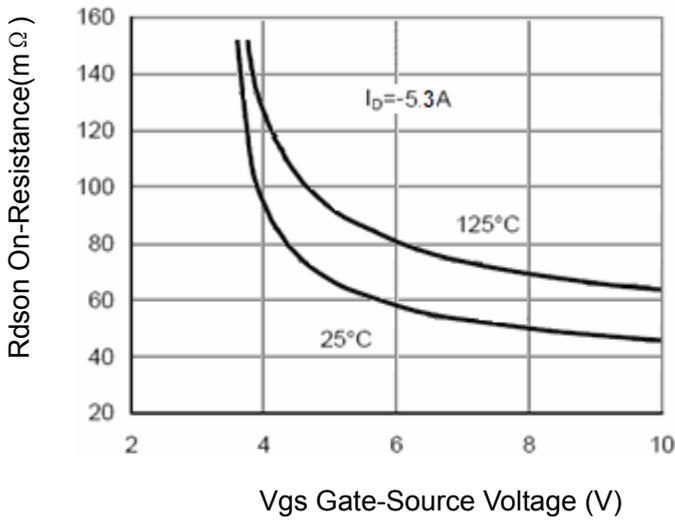
Figure 6 Drain-Source On-Resistance



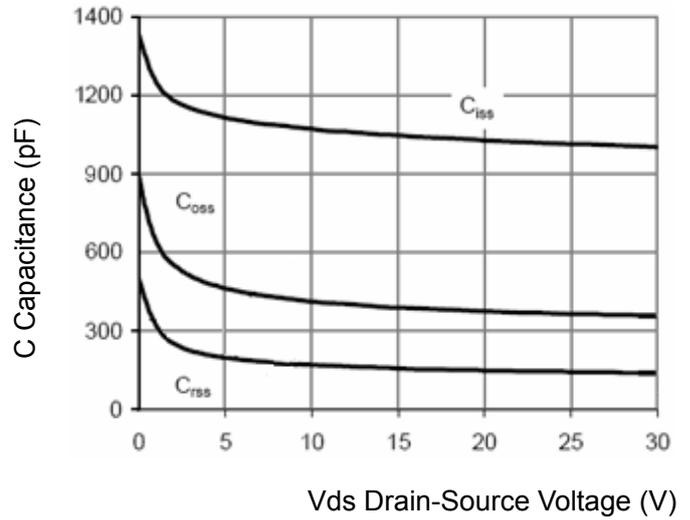
Vgs Gate-Source Voltage (V)
Figure 7 Transfer Characteristics



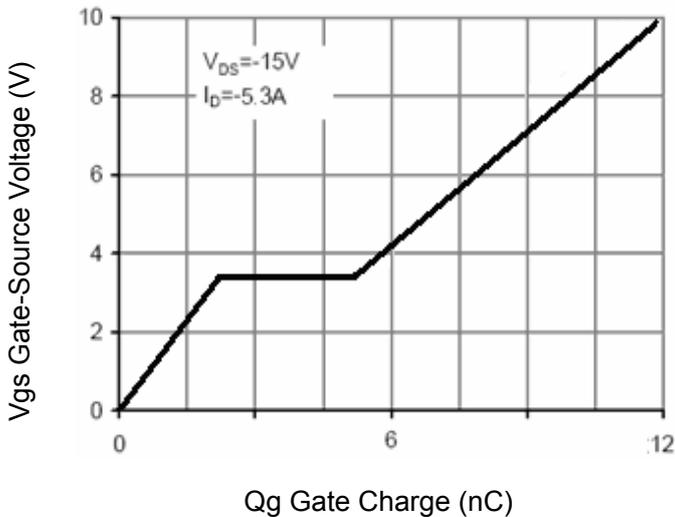
T_J -Junction Temperature(°C)
Figure 8 Drain-Source On-Resistance



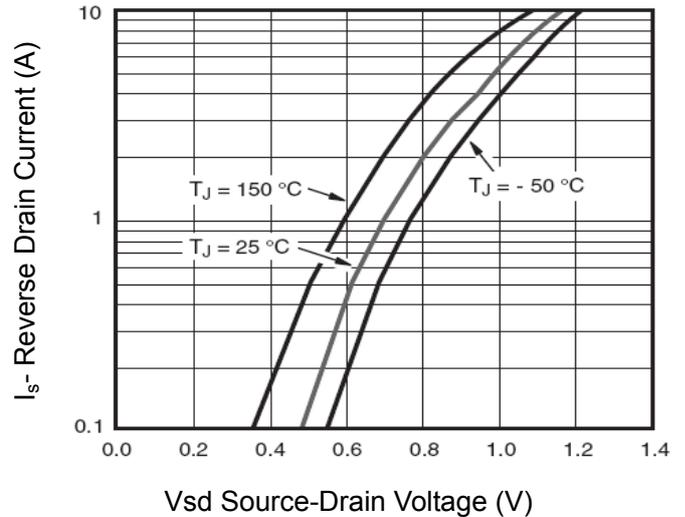
Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs



Vds Drain-Source Voltage (V)
Figure 10 Capacitance vs Vds



Qg Gate Charge (nC)
Figure 11 Gate Charge



Vsd Source-Drain Voltage (V)
Figure 12 Source- Drain Diode Forward

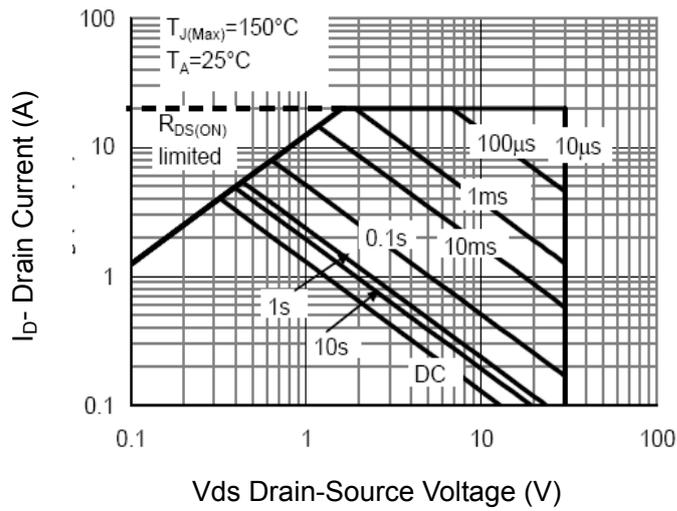


Figure 13 Safe Operation Area

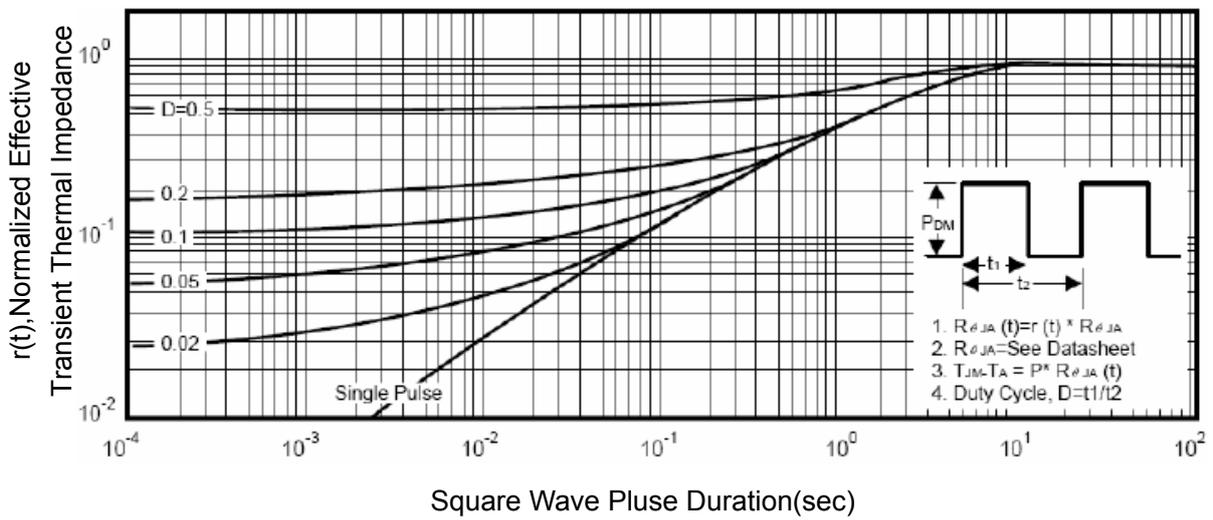
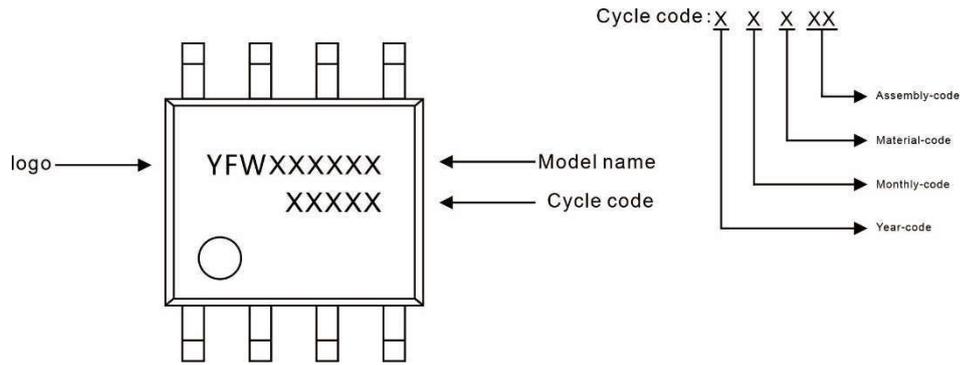


Figure 14 Normalized Maximum Transient Thermal Impedance

Marking Diagram



Ordering information

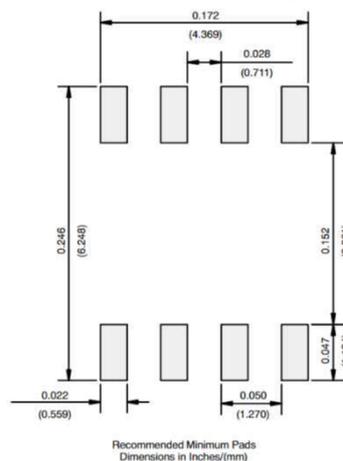
Package	Packing Description	Packing Quantity
SOP-8	Tape/Reel, 13" reel	3000PCS/Reel 30000PCS/Carton

Package Dimensions

SOP-8

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.35	1.50	0.053	0.059
b	0.35	0.55	0.014	0.022
c	0.15	0.25	0.006	0.010
D	4.80	5.00	0.189	0.197
D1	3.10	3.50	0.122	0.138
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
E2	2.20	2.60	0.087	0.102
e	1.27 (BSC)		0.050 (BSC)	
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

The recommended mounting pad size



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